

Inventor: John T. Moore

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Title: Methods of Forming Oxide Regions Over Semiconductor Substrates, and Methods of Forming Transistors Associated with Semiconductor Substrates

Assignee: Micron Technology, Inc.

Serial No.: 09/602,395

Filed: June 22, 2000

**INFORMATION DISCLOSURE STATEMENT**

**PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98**

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, the Examiner's attention is directed to the references listed on the attached Form PTO-1449 and copies of which are attached. No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Respectfully submitted,

Date: 3/23/01

Attorney:

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